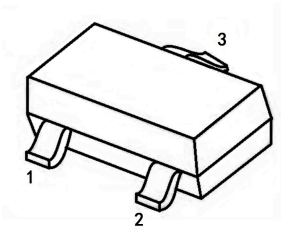
MMBT5401

TRANSISTOR (PNP)

FEATURES

- Complementary to MMBT5551
- Ideal for Medium Power Amplification and Switching

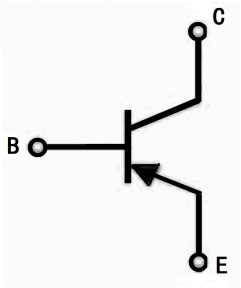
SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

MARKING: 2L

CIRCUIT DIAGRAM



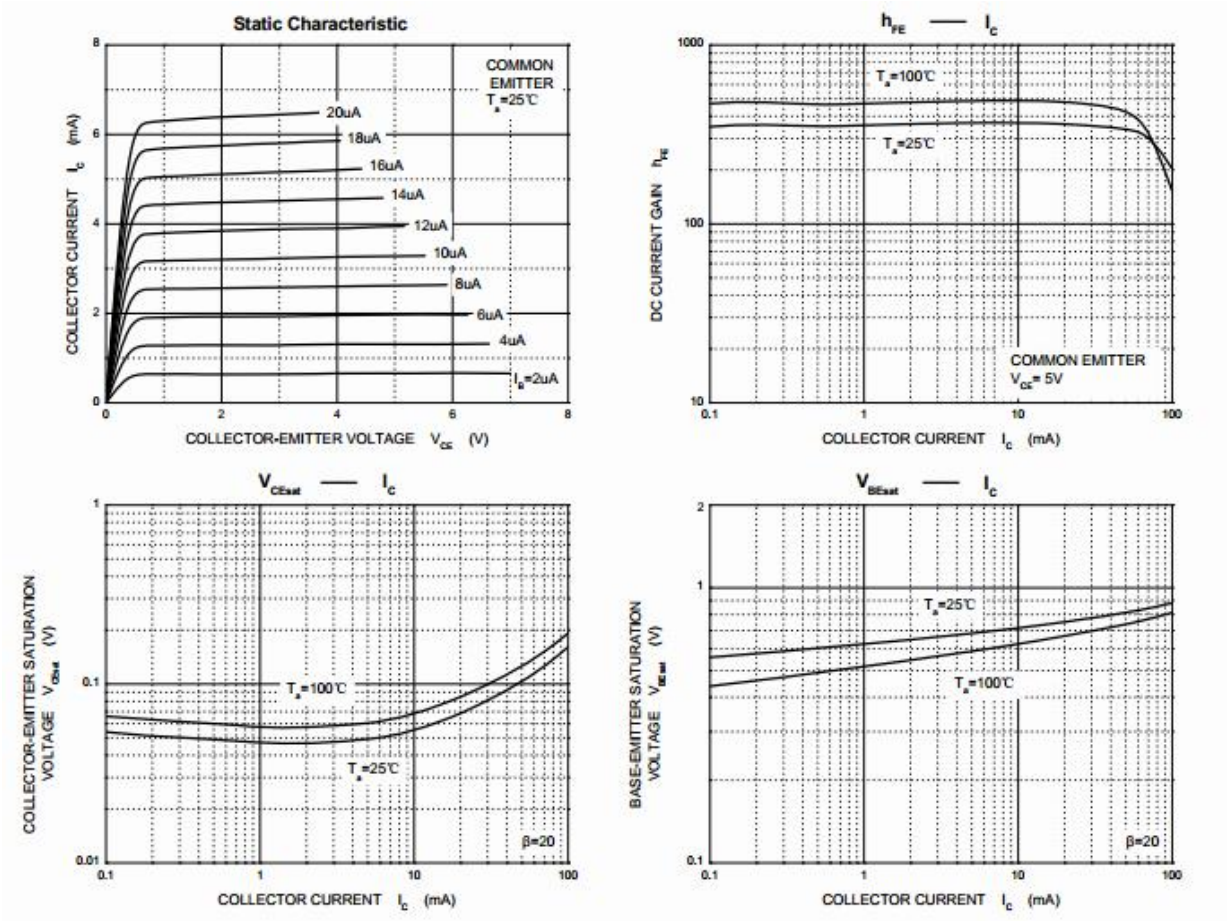
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_{CM}	-0.6	A
Power Dissipation	P_D	0.625	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55~150	℃

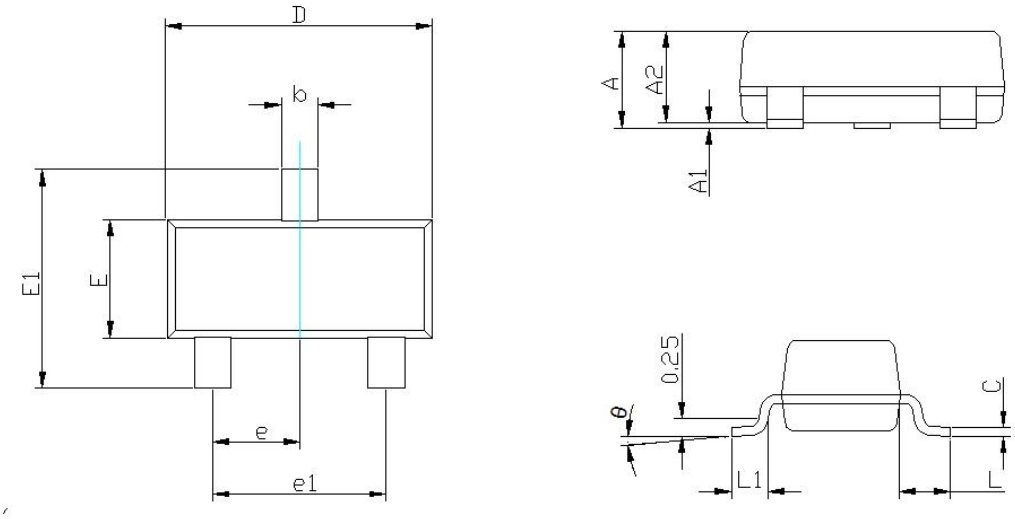
ELECTRICAL CHARACTERISTICS Ta=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit
Emitter-base breakdown voltage	BV_{EBO}	I_E=-100uA, I_C=0	-5		V
Collector-base breakdown voltage	BV_{CBO}	I_C=-100uA, I_E=0	-160		V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=-1mA, I_B=0	-150		V
Emitter cut-off current	I_{EBO}	V_{EB}=-4V, I_C=0		-0.1	uA
Collector cut-off current	I_{CBO}	V_{CB}=-140V, I_E=0		-0.1	uA
Collector cut-off current	I_{CEO}	V_{CE}=-120V, I_B=0		-0.1	uA
Collector-emitter saturation voltage	V_{CESAT}	I_C=-50mA, I_B=-5mA		-1.0	V
Base-emitter saturation voltage	V_{BESAT}	I_C=-50mA, I_B=-5mA		-2.0	V
DC current gain	h_{fe}	V_{CE}=-5V, I_C=-10mA	100	200	
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA F=30MHZ	100		MHZ

TYPICAL CHARACTERISTICS



SOT-23 PACKAGE OUTLINE DRAWING



SYMBOL	MILLIMETERTS		INCHES	
	MIN	MAX	MIN	MAX
A	0.900	1.15	0.035	0.045
A1	0.000	0.125	0.000	0.005
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF（0.4-0.6）		0.022REF（0.016-0.024）	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°